

FAN7392 High-Current, High- and Low-Side, Gate-Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- 3A/3A Sourcing/Sinking Current Driving Capability
- Common-Mode dv/dt Noise Canceling Circuit
- 3.3V Logic Compatible
- Separate Logic Supply (V_{DD}) Range from 3.3V to 20V
- Under-Voltage Lockout for V_{CC} and V_{BS}
- Cycle-by-Cycle Edge-Triggered Shutdown Logic
- Matched Propagation Delay for Both Channels
- Outputs In-phase with Input Signals
- Available in 14-DIP and 16-SOP (Wide) Packages

Applications

- High-Speed Power MOSFET and IGBT Gate Driver
- Server Power Supply
- Uninterrupted Power Supply (UPS)
- Telecom System Power Supply
- Distributed Power Supply
- Motor Drive Inverter

Description

The FAN7392 is a monolithic high- and low-side gate drive IC, that can drive high-speed MOSFETs and IGBTs that operate up to +600V. It has a buffered output stage with all NMOS transistors designed for high pulse current driving capability and minimum cross-conduction. Fairchild's high-voltage process and common-mode noise canceling techniques provide stable operation of the highside driver under high dv/dt noise circumstances. An advanced level-shift circuit offers high-side gate driver operation up to V_S=-9.8V (typical) for V_{BS}=15V. Logic inputs are compatible with standard CMOS or LSTTL output, down to 3.3V logic. The UVLO circuit prevents malfunction when V_{CC} and V_{BS} are lower than the specified threshold voltage. The high-current and low-output voltage drop feature makes this device suitable for halfand full-bridge inverters, like switching-mode power supply and high-power DC-DC converter applications.

14-PDIP

16-SOP





Part Number	Operating Temperature Range	Package	Packing Method
FAN7392N		14-PDIP	Tube
FAN7392M	-40°C to +125°C	16-SOP	Tube
FAN7392MX		10-30P	Tape and Reel









Pin Definitions

14-Pin	16-Pin	Name	Description	
1	1	LO	Low-Side Driver Output	
2	2	COM	Low-Side Return	
3	3	V _{CC}	Low-Side Supply Voltage	
5	6	V _S	High-Voltage Floating Supply Return	
6	7	VB	High-Side Floating Supply	
7	8	НО	High-Side Driver Output	
9	11	V _{DD}	Logic Supply Voltage	
10	12	HIN	Logic Input for High-Side Gate Driver Output	
11	13	SD	Logic Input for Shutdown Function	
12	14	LIN	Logic Input for Low-Side Gate Driver Output	
13	15	V _{SS}	Logic Ground	
4,8,14	4, 5, 9, 10, 16	NC	NC No Connect	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}C$ unless otherwise specified.

Symbol	Characteristics		Min.	Max.	Unit
V _B	High-Side Floating Supply Voltage		-0.3	625.0	V
Vs	High-Side Floating Offset Voltage		V _B -25.0	V _B +0.3	V
V _{HO}	High-Side Floating Output Voltage		V _S -0.3	V _B +0.3	V
V _{CC}	Low-Side Supply Voltage		-0.3	25.0	V
V _{LO}	Low-Side Floating Output Voltage		-0.3	V _{CC} +0.3	V
V _{DD}	Logic Supply Voltage		-0.3	V _{SS} +25.0	V
V _{SS}	Logic Supply Offset Voltage		V _{CC} -25.0	V _{CC} +0.3	V
V _{IN}	Logic Input Voltage (HIN, LIN and SD)		V _{SS} -0.3	V _{DD} +0.3	V
dV _S /dt	Allowable Offset Voltage Slew Rate			±50	V/ns
D	Power Dissipation ^(1, 2, 3)	14-PDIP		1.6	W
PD	Power Dissipation (, , , , ,	16-SOP		1.3	vv
0	θ_{JA} Thermal Resistance $\frac{14-PDIP}{16-SOP}$			75	0000
θ _{JA}				95	°C/W
TJ	Maximum Junction Temperature			+150	°C
T _{STG}	Storage Temperature		-55	+150	°C

Notes:

- 1. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- 2. Refer to the following standards:
 - JESD51-2: Integral circuits thermal test method environmental conditions, natural convection; and JESD51-3: Low effective thermal conductivity test board for leaded surface-mount packages.
- 3. Do not exceed power dissipation (P_D) under any circumstances.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
VB	High-Side Floating Supply Voltage	V _S +10	V _S +20	V
VS	High-Side Floating Supply Offset Voltage	6-V _{CC}	600	V
V _{HO}	High-Side Output Voltage	V _S	VB	V
V _{CC}	Low-Side Supply Voltage	10	20	V
V_{LO}	Low-Side Output Voltage	0	V _{CC}	V
V _{DD}	Logic Supply Voltage	V _{SS} +3	V _{SS} +20	V
V _{SS}	V _{SS} Logic Supply Offset Voltage		5	V
V _{IN}	Logic Input Voltage	V _{SS}	V _{DD}	V
T _A	Operating Ambient Temperature	-40	+125	°C

Electrical Characteristics

 $V_{BIAS}(V_{CC}, V_{BS}, V_{DD})=15.0V$, $V_{SS}=COM=0V$ and $T_A=25^{\circ}C$, unless otherwise specified. The V_{IH} , V_{IL} , and I_{IN} parameters are referenced to V_{SS} and are applicable to the respective input leads: HIN, LIN, and SD. The V_O and I_O parameters are referenced to V_S and COM and are applicable to the respective output leads: HO and LO.

Symbol	Characteristics	Test Condition	Min.	Тур.	Max.	Unit
Low-Side	Power Supply Section					<u>. </u>
I _{QCC}	Quiescent V _{CC} Supply Current	V _{IN} =0V or V _{DD}		40	80	μA
I _{QDD}	Quiescent V _{DD} Supply Current	V _{IN} =0V or V _{DD}			10	μA
I _{PCC}	Operating V _{CC} Supply Current	f _{IN} =20kHz, rms, V _{IN} =15V _{PP}		430		μA
I _{PDD}	Operating V _{DD} Supply Current	f _{IN} =20kHz, rms, V _{IN} =15V _{PP}		300		μA
I _{SD}	Shutdown Supply Current	S _D =V _{DD}		120		μA
V _{CCUV+}	V _{CC} Supply Under-Voltage Positive-Going Threshold Voltage	V _{IN} =0V, V _{CC} =Sweep	7.7	8.8	9.9	V
V _{CCUV-}	V _{CC} Supply Under-Voltage Negative-Going Threshold Voltage	V _{IN} =0V, V _{CC} =Sweep	7.3	8.4	9.5	V
V _{CCUVH}	V _{CC} Supply Under-Voltage Lockout Hysteresis Voltage	V _{IN} =0V, V _{CC} =Sweep		0.4		V
Bootstra	pped Supply Section					
I _{QBS}	Quiescent V _{BS} Supply Current	V _{IN} =0V or V _{DD}		60	130	μA
I _{PBS}	Operating V _{BS} Supply Current	f _{IN} =20kHz, rms value		500		μA
V _{BSUV+}	V _{BS} Supply Under-Voltage Positive-Going Threshold Voltage	V _{IN} =0V, V _{BS} =Sweep	7.7	8.8	9.9	V
V _{BSUV-}	V _{BS} Supply Under-Voltage Negative-Going Threshold Voltage	V _{IN} =0V, V _{BS} =Sweep	7.3	8.4	9.5	v
V _{BSUVH}	V _{BS} Supply Under-Voltage Lockout Hysteresis Voltage	V _{IN} =0V, V _{BS} =Sweep		0.4		V
I _{LK}	Offset Supply Leakage Current	V _B =V _S =600V			50	μA
Input Loc	cic Section (HIN, LIN, and SD)				•	
V	Logia "4" Input Throshold Voltage	V _{DD} =3V	2.4			V
V _{IH}	Logic "1" Input Threshold Voltage	V _{DD} =15V	9.5			V
	Lessie (Oliverse) Threads and Matter	V _{DD} =3V			0.8	V
VIL	Logic "0" Input Threshold Voltage	V _{DD} =15V			4.5	V
I _{IN+}	Logic Input High Bias Current	V _{IN} =V _{DD}		20	40	μΑ
I _{IN-}	Logic Input Low Bias Current	V _{IN} =0V			3	μA
R _{IN}	Logic Input Pull-Down Resistance		375	750		KΩ
Gate Driv	ver Output Section				10	
V _{OH}	High-Level Output Voltage (V _{BIAS} - V _O)	No Load (I _O =0A)			1.5	V
V _{OL}	Low-Level Output Voltage	No Load (I _O =0A)			200	mV
I _{O+}	Output High, Short-Circuit Pulsed Current ⁽⁴⁾	V _O =0V, PW ≤10µs	2.5	3.0		Α
I _{O-}	Output Low, Short-Circuit Pulsed Current ⁽⁴⁾	V _O =15V, PW ≤10µs	2.5	3.0		Α
V _{SS} /COM	V _{SS} -COM/COM-V _{SS} Voltage Endurability		-5.0		5.0	V
- V _S	Allowable Negative V _S Pin Voltage for HIN Signal Propagation to HO			-9.8	-7.0	V

Dynamic Electrical Characteristics

 $V_{BIAS}(V_{CC}, V_{BS}, V_{DD}) = 15.0V, V_{SS} = COM = 0V, C_{LOAD} = 1000 pF, T_A = 25^{\circ}C, unless otherwise specified.$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t _{on}	Turn-On Propagation Delay Time	V _S =0V		130	180	ns
t _{off}	Turn-Off Propagation Delay Time	V _S =0V		150	200	ns
t _{sd}	Shutdown propagation Delay Time ⁽⁴⁾			130	180	ns
t _r	Turn-On Rise Time			25	50	ns
t _f	Turn-Off Fall Time			20	45	ns
MT	Delay Matching, HO & LO Turn-On/Off				35	ns

Note:

4. These parameters guaranteed by design.









Switching Time Definitions







Figure 30. Input/Output Timing Diagram







Application Information

Negative V_S Transient

The bootstrap circuit has the advantage of being simple and low cost, but has some limitations. The biggest difficulty with this circuit is the negative voltage present at the emitter of the high-side switching device when highside switch is turned-off in half-bridge application.

If the high-side switch, Q1, turns-off while the load current is flowing to an inductive load, a current commutation occurs from high-side switch, Q1, to the diode, D2, in parallel with the low-side switch of the same inverter leg. Then the negative voltage present at the emitter of the high-side switching device, just before the freewheeling diode, D2, starts clamping, causes load current to suddenly flow to the low-side freewheeling diode, D2, as shown in Figure 34.



Figure 34. Half-Bridge Application Circuits

This negative voltage can be trouble for the gate driver's output stage, there is the possibility to develop an overvoltage condition of the bootstrap capacitor, input signal missing and latch-up problems because it directly affects the source V_S pin of the gate driver, as shown in Figure 35. This undershoot voltage is called "negative V_S transient".





Figure 36 and Figure 37 show the commutation of the load current between high-side switch, Q1, and low-side freewheelling diode, D3, in same inverter leg. The parasitic inductances in the inverter circuit from the die wire bonding to the PCB tracks are jumped together in L_C and L_E for each IGBT. When the high-side switch, Q1, and low-side switch, Q4, are turned on, the VS1 node is below DC+ voltage by the voltage drops associated with the power switch and the parasitic inductances of the circuit due to load current is flows from Q1 and Q4, as shown in Figure 36. When the high-side switch, Q1, is turned off and Q4, remained turned on, the load current to flows the low-side freewheeling diode, D3, due to the inductive load connected to VS1 as shown in Figure 37. The current flows from ground (which is connected to the COM pin of the gate driver) to the load and the negative voltage present at the emitter of the high-side switching device.

In this case, the COM pin of the gate driver is at a higher potential than the V_S pin due to the voltage drops associated with freewheeling diode, D3, and parasitic elements, L_{C3} and L_{F3} .









The FAN7392 has a negative $\rm V_{S}$ transient performance curve, as shown in Figure 38.



Figure 38. Negative V_S Transient Chracteristic

Even though the FAN7392 has been shown able to handle these negative V_S tranient conditions, it is strongly recommended that the circuit designer limit the negative V_S transient as much as possible by careful PCB layout to minimized the value of parasitic elements and component use. The amplitude of negative V_S voltage is proportional to the parasitic inductances and the turn-off speed, di/dt, of the switching device.

General Guidelines

Printed Circuit Board Layout

The relayout recommended for minimized parasitic elements is as follows:

- Direct tracks between switches with no loops or deviation.
- Avoid interconnect links. These can add significant inductance.
- Reduce the effect of lead-inductance by lowering package height above the PCB.
- Consider co-locating both power switches to reduce track length.
- To minimize noise coupling, the ground plane should not be placed under or near the high-voltage floating side.
- To reduce the EM coupling and improve the power switch turn-on/off performance, the gate drive loops must be reduced as much as possible.

Placement of Components

The recommended placement and selection of component as follows:

- Place a bypass capacitor between the V_{DD} and V_{SS} pins. A ceramic 1µF capacitor is suitable for most applications. This component should be placed as close as possible to the pins to reduce parasitic elements.
- The bypass capacitor from V_{CC} to COM supports both the low-side driver and bootstrap capacitor recharge. A value at least ten times higher than the bootstrap capacitor is recommended.
- The bootstrap resistor, R_{BOOT} , must be considered in sizing the bootstrap resistance and the current developed during initial bootstrap charge. If the resistor is needed in series with the bootstrap diode, verify that V_B does not fall below COM (ground). Recommended use is typically 5 ~ 10 Ω that increase the V_{BS} time constant. If the votage drop of of bootstrap resistor and diode is too high or the circuit topology does not allow a sufficient charging time, a fast recovery or ultra-fast recovery diode can be used.
- The bootstrap capacitor, C_{BOOT}, uses a low-ESR capacitor, such as ceramic capacitor.

It is stongly recommended that the placement of components is as follows:

- Place components tied to the floating voltage pins (V_B and V_S) near the respective high-voltage portions of the device and the FAN7392. NC (not connected) pins in this package maximize the distance between the high-voltage and low-voltage pins (*see Figure 5*).
- Place and route for bypass capacitors and gate resistors as close as possible to gate drive IC.
- Locate the bootstrap diode, D_{BOOT}, as close as possible to bootstrap capacitor, C_{BOOT}.
- The bootstrap diode must use a lower forward voltage drop and minimal switching time as soon as possible for fast recovery or ultra-fast diode.



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